

Small Signal Product

## 300mW, NPN Small Signal Transistor

### FEATURES

- Epitaxial planar die construction
- Surface device type mounting
- Moisture sensitivity level 1
- Matte Tin (Sn) lead finish with Nickel (Ni) underplate
- Pb free version and RoHS compliant
- Packing code with suffix "G" means green compound (halogen-free)

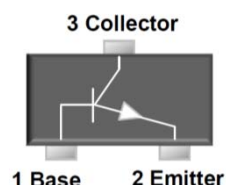


SOT-23



### MECHANICAL DATA

- Case: SOT- 23, molded plastic
- Terminal: Matte tin plated, lead free, solderable per MIL-STD-202, Method 208 guaranteed
- High temperature soldering guaranteed: 260°C/10s
- Weight: 8 mg (approximately)
- Marking Code: 1E.



| MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (T <sub>A</sub> =25°C unless otherwise noted) |                                   |             |      |
|----------------------------------------------------------------------------------------------|-----------------------------------|-------------|------|
| PARAMETER                                                                                    | SYMBOL                            | VALUE       | UNIT |
| Power Dissipation                                                                            | P <sub>D</sub>                    | 300         | mW   |
| Collector-Base Voltage                                                                       | V <sub>CBO</sub>                  | 60          | V    |
| Collector-Emitter Voltage                                                                    | V <sub>CEO</sub>                  | 40          | V    |
| Emitter-Base Voltage                                                                         | V <sub>EBO</sub>                  | 6           | V    |
| Collector Current                                                                            | I <sub>C</sub>                    | 200         | mA   |
| Junction and Storage Temperature Range                                                       | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

Notes: Valid provided that electrodes are kept at ambient temperature

| PARAMETER                            |                       |                         |                            | SYMBOL                   | MIN            | MAX  | UNIT |     |
|--------------------------------------|-----------------------|-------------------------|----------------------------|--------------------------|----------------|------|------|-----|
| Collector-Base Breakdown Voltage     |                       | I <sub>C</sub> = 10 μA  | I <sub>E</sub> = 0         | V <sub>(BR)CBO</sub>     | 60             | -    | V    |     |
| Collector-Emitter Breakdown Voltage  |                       | I <sub>C</sub> = 1 mA   | I <sub>B</sub> = 0         | V <sub>(BR)CEO</sub>     | 40             | -    | V    |     |
| Emitter-Base Breakdown Voltage       |                       | I <sub>E</sub> = 10 μA  | I <sub>C</sub> = 0         | V <sub>(BR)EBO</sub>     | 6              | -    | V    |     |
| Collector Cut-off Current            |                       | V <sub>CB</sub> = 60 V  | I <sub>E</sub> = 0         | I <sub>CBO</sub>         | -              | 0.1  | μA   |     |
| Collector Cut-off Current            |                       | V <sub>CE</sub> = 30 V  | V <sub>BE(OFF)</sub> = 3 V | I <sub>CEO</sub>         | -              | 50   | nA   |     |
| Emitter Cut-off Current              |                       | V <sub>EB</sub> = 5 V   | I <sub>C</sub> = 0         | I <sub>EBO</sub>         | -              | 0.1  | μA   |     |
| DC Current Gain                      | V <sub>CE</sub> = 1 V | I <sub>C</sub> = 10 mA  | h <sub>FE</sub>            | 100                      | 400            |      |      |     |
|                                      | V <sub>CE</sub> = 1 V | I <sub>C</sub> = 50 mA  |                            | 60                       | -              |      |      |     |
|                                      | V <sub>CE</sub> = 1 V | I <sub>C</sub> = 100 mA |                            | 30                       | -              |      |      |     |
| Collector-Emitter Saturation Voltage |                       | I <sub>C</sub> = 50 mA  | I <sub>B</sub> = 5 mA      | V <sub>CE(sat)</sub>     | -              | 0.3  | V    |     |
| Base-Emitter Saturation Voltage      |                       | I <sub>C</sub> = 50 mA  | I <sub>B</sub> = 5 mA      | V <sub>BE(sat)</sub>     | -              | 0.95 | V    |     |
| Transition frequency                 |                       | V <sub>CE</sub> = 20 V  | I <sub>C</sub> = 10 mA     | f = 100MHz               | f <sub>T</sub> | 250  | -    | MHz |
| Delay time                           | V <sub>CC</sub> = 3 V | V <sub>BE</sub> = 0.5 V | I <sub>C</sub> = 10 mA     | I <sub>B1</sub> = 1.0 mA | t <sub>d</sub> | -    | 35   | ns  |
| Rise time                            |                       |                         |                            |                          | t <sub>r</sub> | -    | 35   | ns  |
| Storage time                         |                       |                         |                            |                          | t <sub>s</sub> | -    | 200  | ns  |
| Fall time                            |                       |                         |                            |                          | t <sub>f</sub> | -    | 50   | ns  |

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### RATINGS AND CHARACTERISTICS CURVES

( $T_A=25^\circ\text{C}$  unless otherwise noted)

Fig.1 Typical Pulsed Current Gain vs. Collector Current

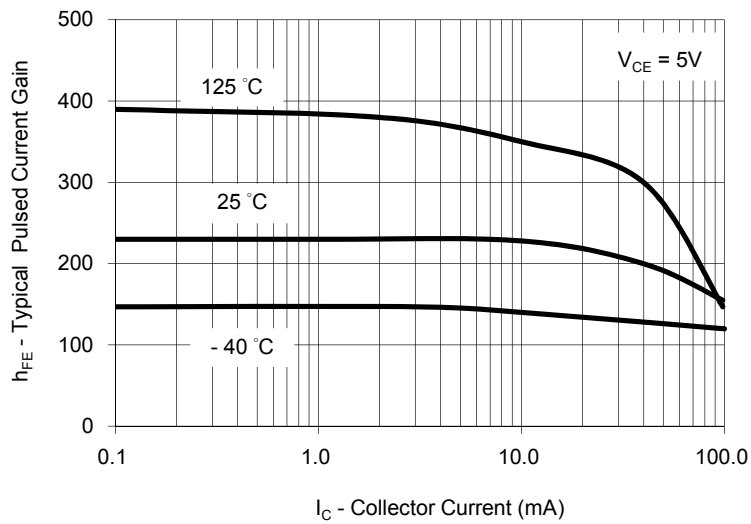


Fig. 2 Collector-Emitter Saturation Voltage vs. Collector Current

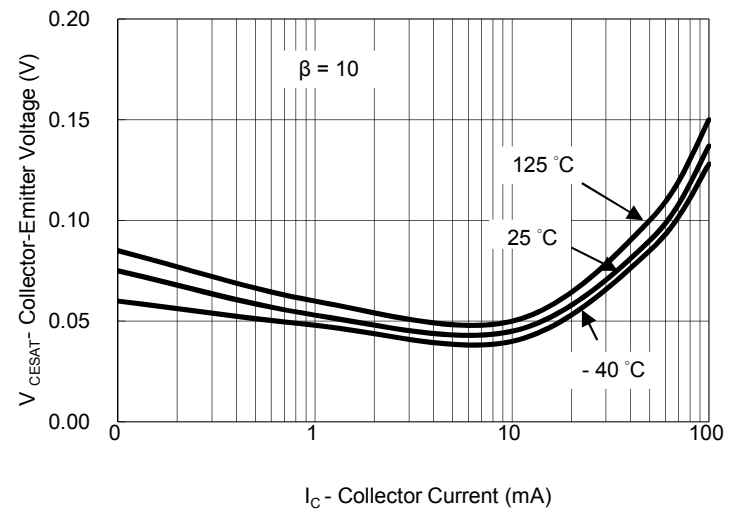


Fig. 3 Base-Emitter Saturation Voltage vs. Collector Current

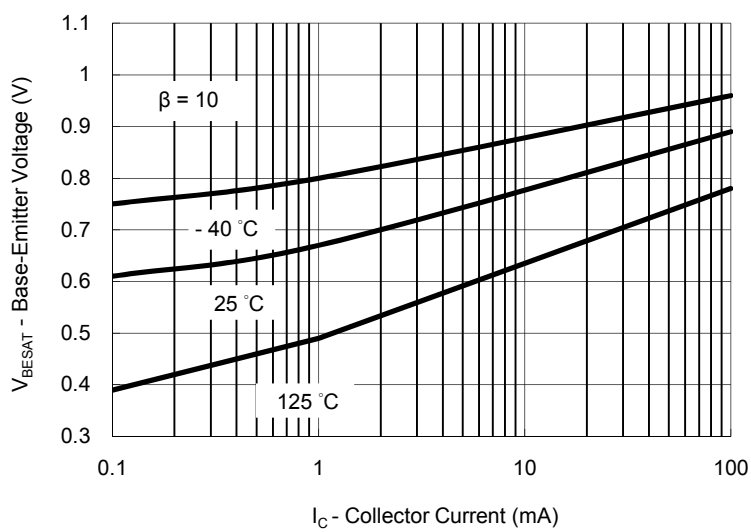


Fig. 4 Base-Emitter On Voltage vs. Collector Current

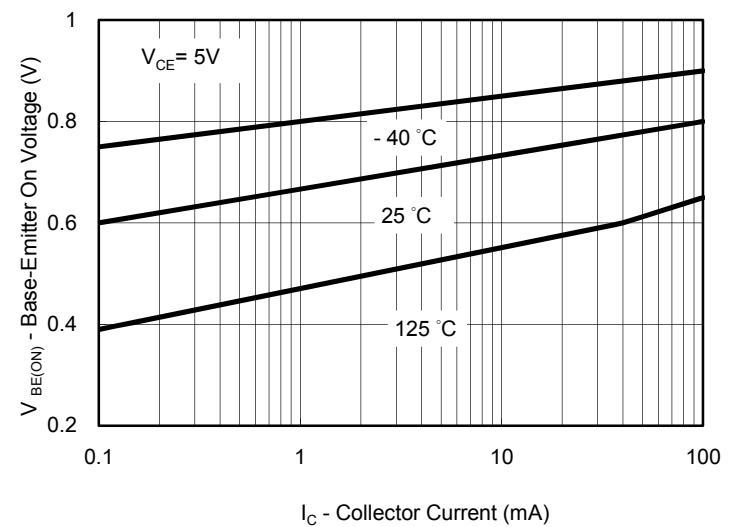


Fig. 5 Collector-Cutoff Current vs. Ambient Temperature

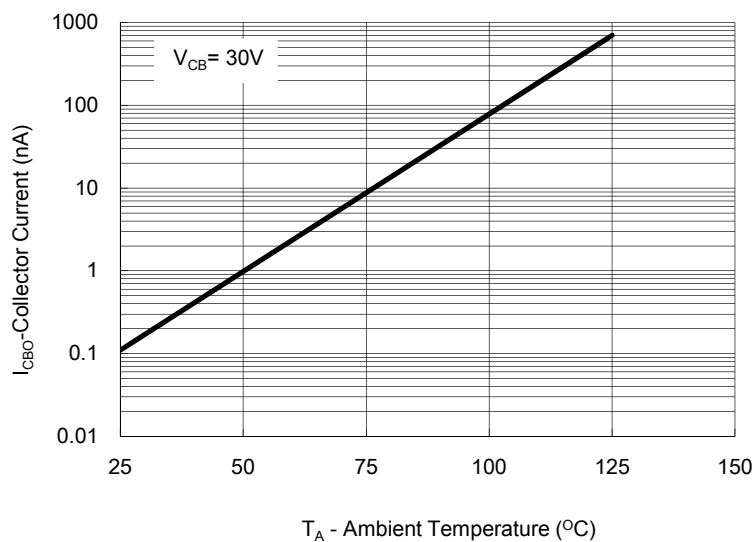
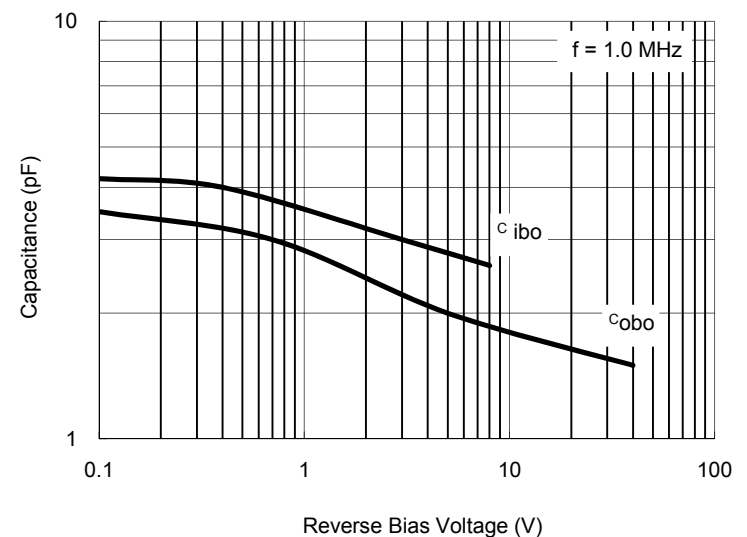


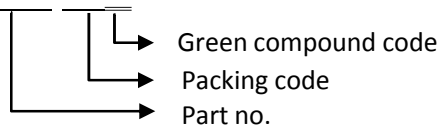
Fig. 6 Capacitance vs. Reverse Bias Voltage



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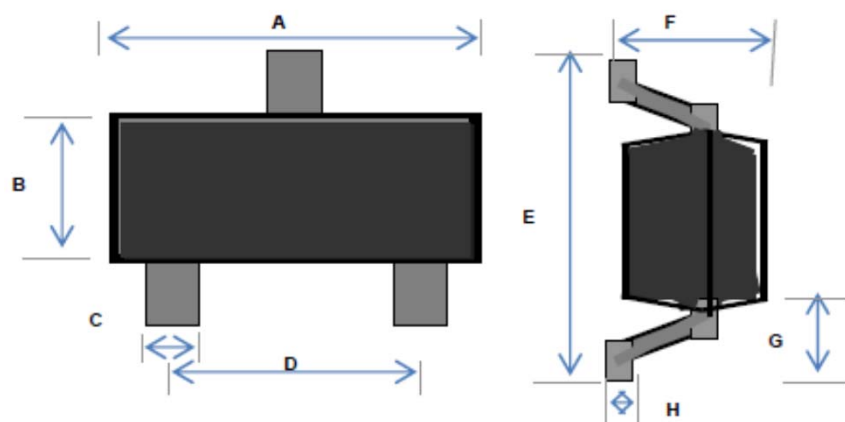
## ORDER INFORMATION (EXAMPLE)

MMBT3904L RFG



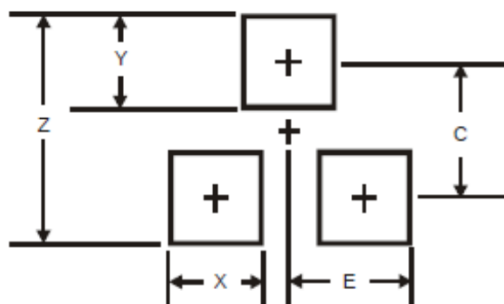
## PACKAGE OUTLINE DIMENSIONS

### SOT-23



| DIM. | Unit(mm) |      | Unit(inch) |       |
|------|----------|------|------------|-------|
|      | Min      | Max  | Min        | Max   |
| A    | 2.70     | 3.10 | 0.106      | 0.122 |
| B    | 1.10     | 1.50 | 0.043      | 0.059 |
| C    | 0.30     | 0.51 | 0.012      | 0.020 |
| D    | 1.78     | 2.04 | 0.070      | 0.080 |
| E    | 2.10     | 2.64 | 0.083      | 0.104 |
| F    | 0.89     | 1.30 | 0.035      | 0.051 |
| G    | 0.55 REF |      | 0.022 REF  |       |
| H    | 0.10 REF |      | 0.004 REF  |       |

## SUGGEST PAD LAYOUT



| DIM | Unit (mm) | Unit (inch) |
|-----|-----------|-------------|
|     | TYP       | TYP         |
| Z   | 2.90      | 0.114       |
| X   | 0.80      | 0.031       |
| Y   | 0.90      | 0.035       |
| C   | 2.00      | 0.079       |
| E   | 1.35      | 0.053       |

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